



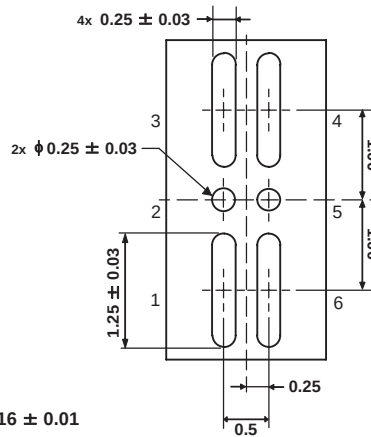
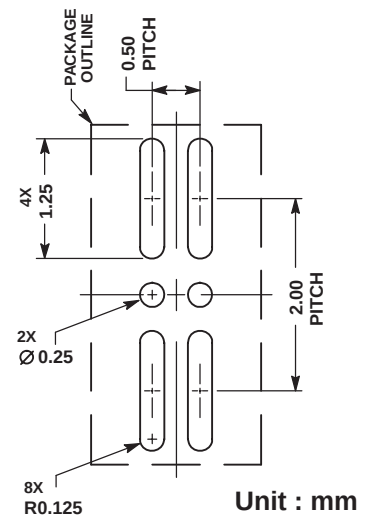
Dual N-Channel Enhancement Mode Field Effect Transistor

VSSS	IS	RSS(ON) (mΩ) Typ
12V	27A	2.5 @ VGS=4.5V
		2.6 @ VGS=4.0V
		2.8 @ VGS=3.8V
		3.3 @ VGS=3.1V
		4.0 @ VGS=2.5V

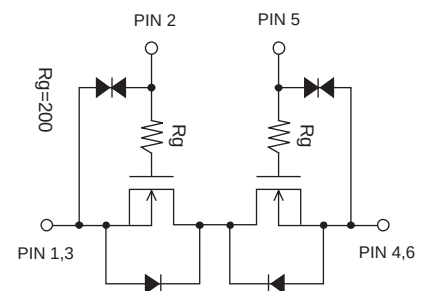
- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- Wafer level CSP.
- ESD Protected.

Technical drawing of a rectangular component with dimensions and labels:

- Overall width: 1.77
- Overall height: 3.54
- Internal dimensions (from top edge):
 - 4
 - 5
 - 6
- Internal dimensions (from right edge):
 - 3
 - 2
 - 1
- Internal text: 8611 Date Code
- Mark area (indicated by an arrow pointing to the bottom-left corner of the internal rectangle)
- 1-pin index mark S1 (indicated by an arrow pointing to a small circle at the bottom-right corner of the internal rectangle)
- Dimension 2x $\phi 0.25$ (indicated by an arrow pointing to the small circle)
- Bottom dimension: 0.16 ± 0.01



Symbol	Parameter	Limit	Units
V _{SSS}	Source-Source Voltage	12	V
V _{GSS}	Gate-Source Voltage	±8	V
I _S	Source Current-Continuous ^a	27	A
I _{SP}	-Pulsed ^b	100	A
P _T	Total Power Dissipation ^a	2.5	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C



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SC8611

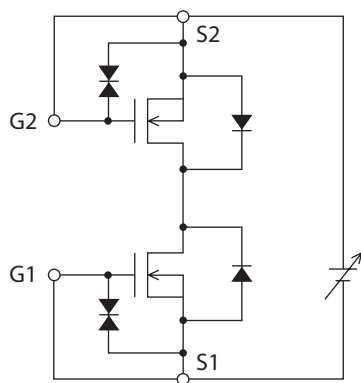
Ver 1.0

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

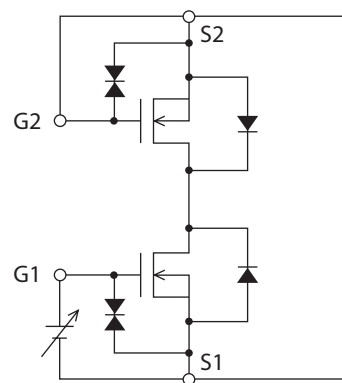
Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{SSS}	Source-Source Breakdown Voltage	V _{GS} =0V, I _S =1mA	12			V
I _{SSS}	Zero Gate Voltage Source Current	V _{SS} =10V, V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±5V, V _{SS} =0V			±1	uA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{SS} =V _{GS} , I _S =1mA	0.5		1.3	V
R _{SS(ON)}	Source-Source On-State Resistance	V _{GS} =4.5V, I _S =5.0A	1.8	2.5	3.2	m ohm
		V _{GS} =4.0V, I _S =5.0A	1.9	2.6	3.2	m ohm
		V _{GS} =3.8V, I _S =5.0A	2.0	2.8	3.3	m ohm
		V _{GS} =3.1V, I _S =5.0A	2.1	3.2	4.4	m ohm
		V _{GS} =2.5V, I _S =5.0A	2.7	4.0	6.3	m ohm
g _{FS}	Forward Transconductance	V _{SS} =6V, I _S =3A		19		S
SWITCHING CHARACTERISTICS ^c						
t _{D(ON)}	Turn-On Delay Time	V _{SS} =6V I _S =3A V _{GS} =4.5V		80		ns
t _r	Rise Time			570		ns
t _{D(OFF)}	Turn-Off Delay Time			38000		ns
t _f	Fall Time			17700		ns
Q _g	Total Gate Charge	V _{SS} =6V, I _S =27A, V _{GS} =4.5V		100		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{FSS}	Diode Forward Voltage	V _{GS} =0V, I _S =3A		0.75	1.2	V
Note a. Mounted on FR4 board of 25.4mm x 25.4mm x 1.0mm. b. Pulse Test: Pulse Width ≤ 10us, Duty Cycle ≤ 1%. c. Guaranteed by design, not subject to production testing.						

Jul,07,2015

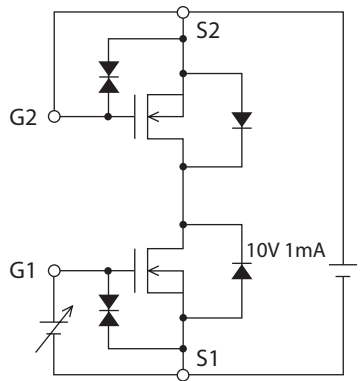
V_{SSS} / I_{SSS}



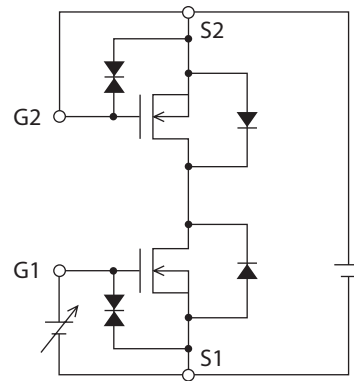
$I_{GSS} (+) / (-)$



$V_{GS} \text{ (off)}$

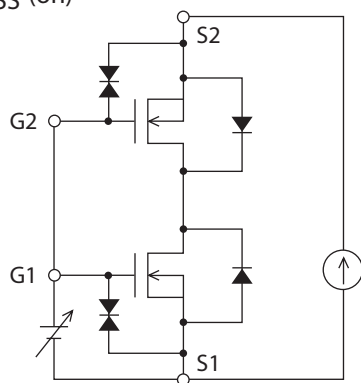


$|y_{fs}|$

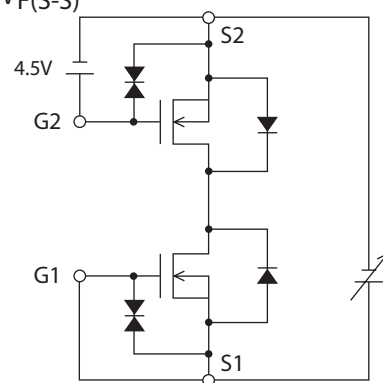


* Note: Connect the measurement terminal reversely if you want to measure the FET2 side.

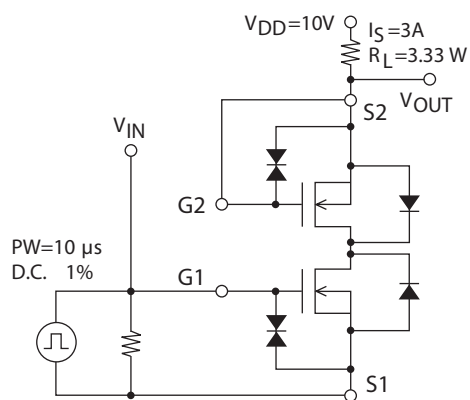
$R_{SS} \text{ (on)}$



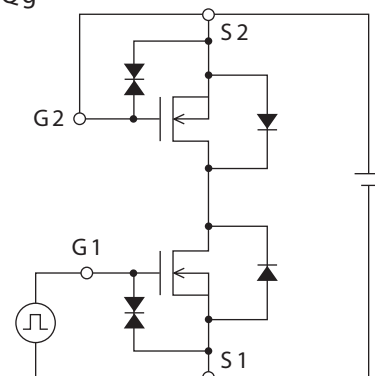
$V_F(S-S)$



$t_d(\text{on}), t_r, t_d(\text{off}), t_f$



Q_g



* Note: Connect the measurement terminal reversely if you want to measure the FET2 side.

TOP MARKING DEFINITION

WLCSP

